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PATENT
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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re application of

Jin JANG et al.

Group Art Unit: 1765

Application No.: 09/350,313

Examiner: R. KUNEMUND

Filed: July 9, 1999

For: METHOD OF CRYSTALLIZING AMORPHOUS SILICON LAYER
AND CRYSTALLIZING APPARATUS THEREOF

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AMENDMENT

Box Non-Fee Amendment

Commissioner of Patents
Washington, D.C. 20231

Dear Sir:

In response to the Examiner's Office Action dated June 26, 2002, the following amendments and remarks are respectfully submitted.

IN THE CLAIMS:

Please amend the claims as follows (A marked-up version of the amended claims is attached):

22. (Amended) A crystallizing apparatus, comprising:

- a chamber having inner space;
- a substrate support arranged in the chamber, the substrate support being used for supporting a substrate having an amorphous silicon layer formed thereon;
- a plasma generating device having a metal source connected to a power supply, the plasma generating device producing plasma inside the chamber by supplying the metal bar with RF or DC power from the power supply to deposit a crystallization catalyst on an exposed surface of the amorphous silicon layer;